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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application)

Applicant: Nakamura et al.)

Serial No.: 09/856,209)

Filed: May 18, 2001)

For: **Silicon Crystal and Production Method
for Silicon Single Crystal Wafer**)

Examiner: Song)

Group Art: 1765)

I hereby certify that this Amendment is being deposited with the United Postal Service as first class mail in an envelope addressed to: Commissioner of Patents, Washington, DC 20231, on August 13, 2002

Gerald T. Shekleton Reg. No. 27,466

AMENDMENT

Box NON-FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The Office Action of May 14, 2002 has been carefully reviewed and the following amendments and remarks are made in response thereto.

IN THE CLAIMS:

Please amend claims 1, 5, 6, 10, and 13 as follows:

1. (amended) A method for producing a silicon single crystal ingot by the Czochralski method, characterized in that by adjusting temperature parameters only during pulling of the silicon single crystal ingot, and performing pulling of a silicon single crystal ingot containing a perfectly crystalline part such that an oxidation induced stacking fault ring appears at a prescribed position in the silicon single crystal ingot, a production efficiency of a perfectly crystalline part of the silicon single crystal ingot and/or of a part of the silicon single crystal ingot which can be used as wafers is improved.

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